General Description

The WSP4409A is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP4409A meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Product Summery

BVDSS	RDSON	ID
-30V	8.0mΩ	-15A

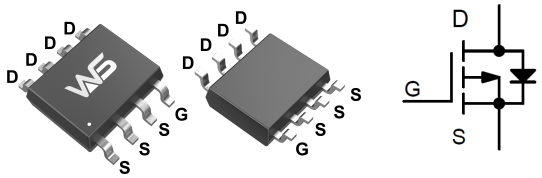
Applications

● Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.
HBM ESD protection level pass 8KV.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_c=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-15	A
I_D@T_c=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-10	A
I_{DM}	Pulsed Drain Current[2]	-70	A
EAS	Single Pulse Avalanche Energy[3]	70	mJ
I_{AS}	Avalanche Current	-38	A
P_D@T_A=25℃	Total Power Dissipation[4]	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	24	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.018	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-15A	---	8	10	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	10	14	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-	-2.7	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	5.04	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-10A	---	15	---	S
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V,V_{GS}=-4.5V,I_D=-15A	---	72	---	nC
Q_{gs}	Gate-Source Charge		---	12	---	
Q_{gd}	Gate-Drain Charge		---	16	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V,V_{GS}=-10V,R_G=6Ω, I_D=-1A ,RL=15Ω	---	16	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	80	---	
T_f	Fall Time		---	14	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	3500	---	pF
C_{oss}	Output Capacitance		---	635	---	
C_{rss}	Reverse Transfer Capacitance		---	645	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=-25V , L=0.5mH , I_{AS}=-38A	30	---	---	mJ

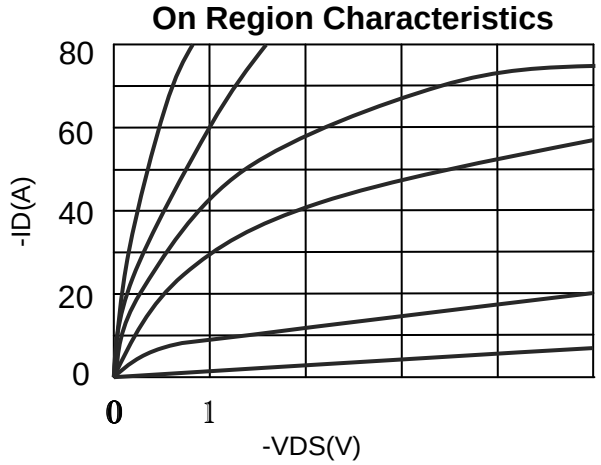
Diode Characteristics

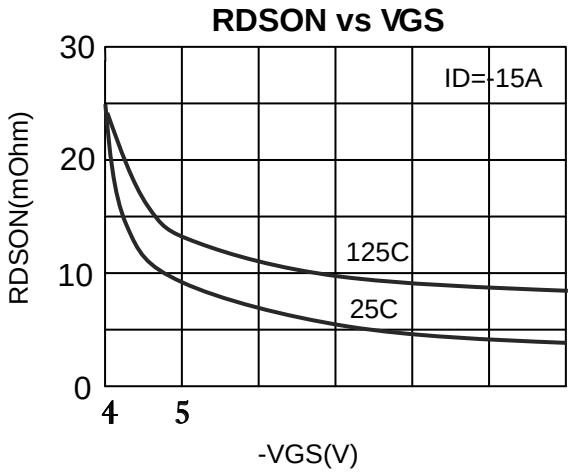
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	-4.0	A
I_{SM}	Pulsed Source Current[2,6]		---	---	-70	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.3	V
t_{rr}	Reverse Recovery Time	I_F=-17.6A,dI/dt=100A/μs,T_J=25℃	---	26	---	nS
Q_{rr}	Reverse Recovery Charge		---	18	---	nC

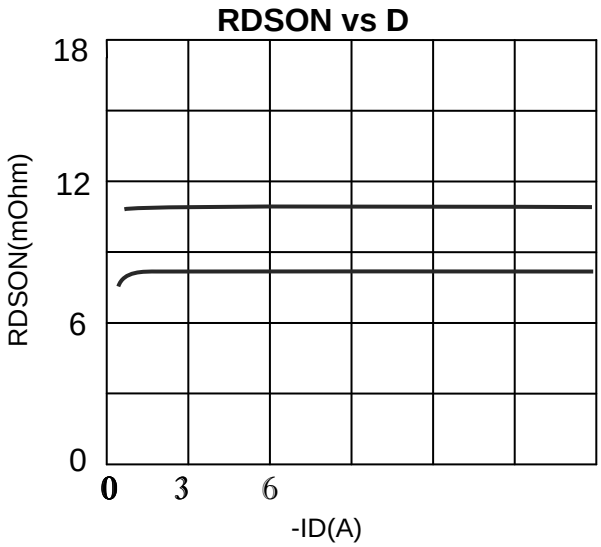
Note :

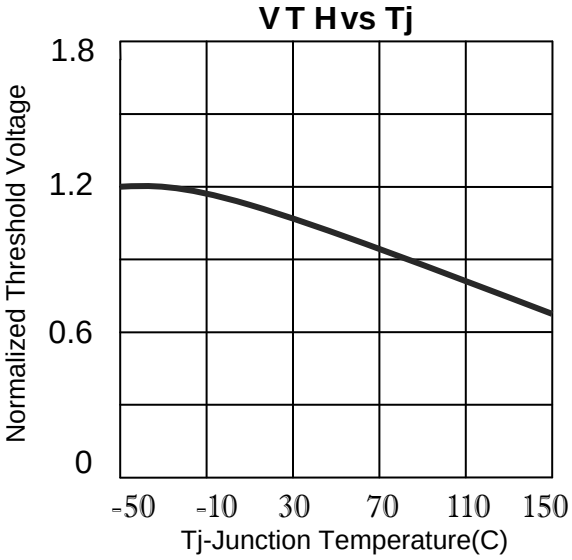
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper, t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is VDD=-25V,VGS=-10V,L=0.5mH,IAS=-38A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

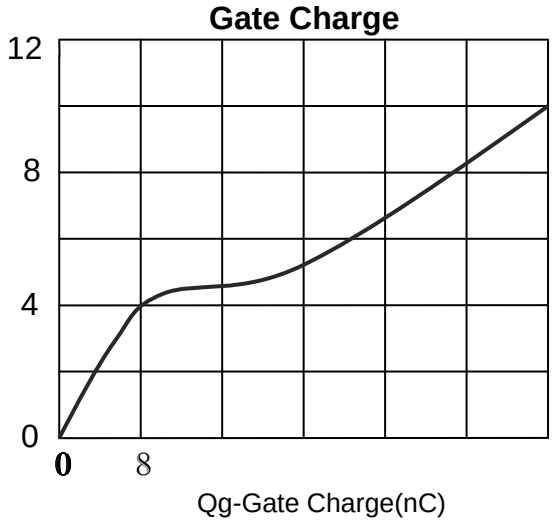
Typical Characteristics

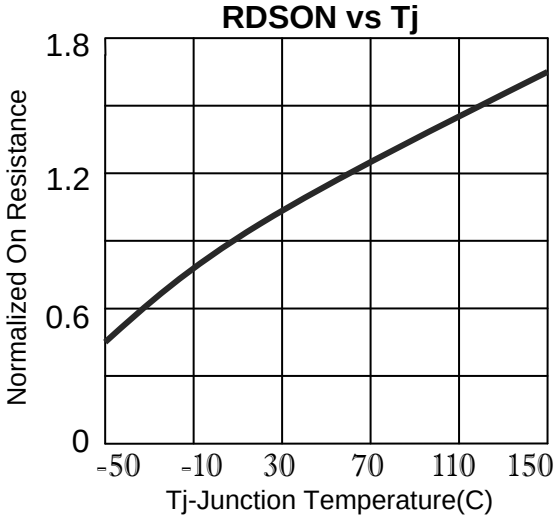


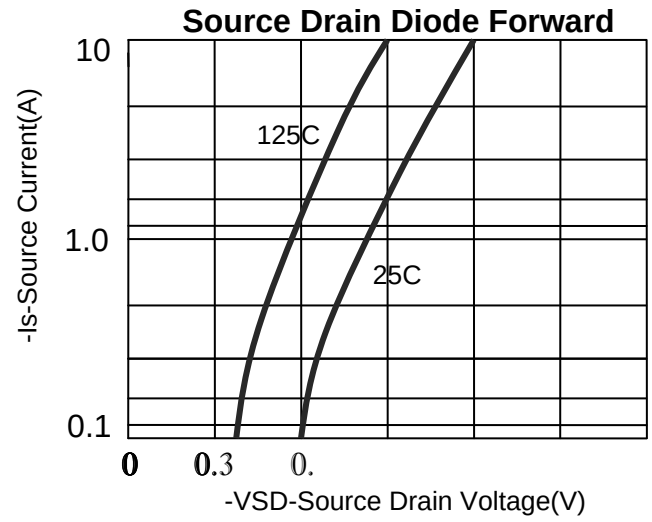


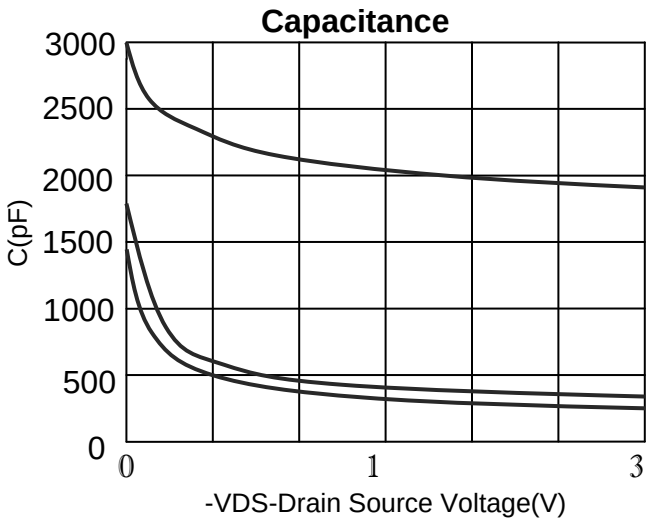


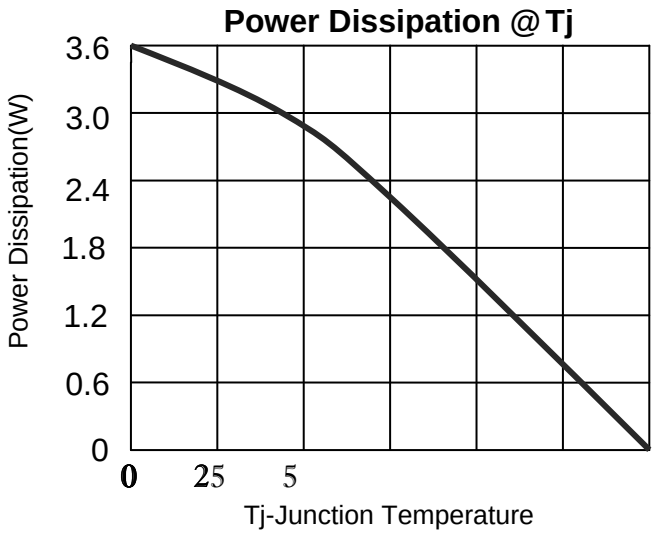


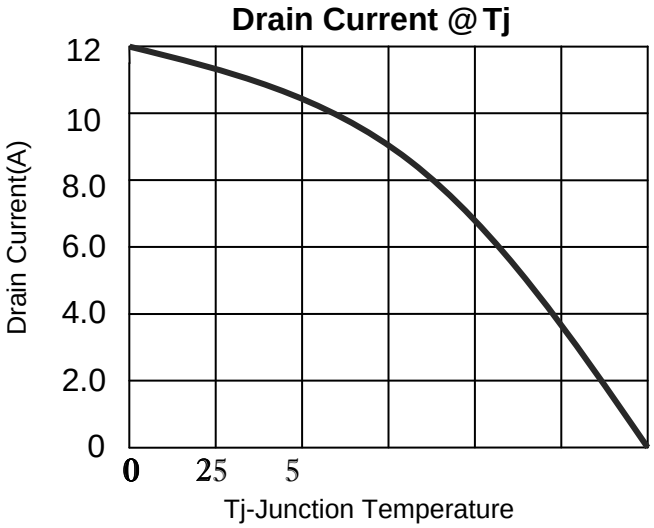


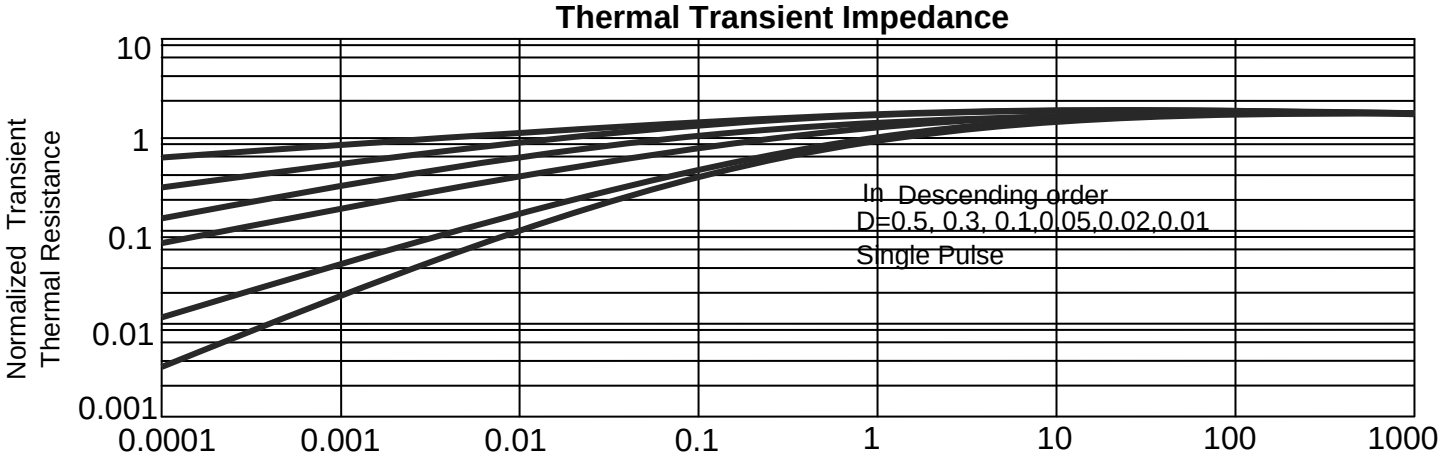



Source Drain Diode Forward
-Is-Source Current(A)
10
1.0
0.1
125C
25C
0
0.3
0.
-VSD-Source Drain Voltage(V)


Capacitance
C(pF)
3000
2500
2000
1500
1000
500
0
0
1
3
-VDS-Drain Source Voltage(V)


Power Dissipation @ Tj
Power Dissipation(W)
3.6
3.0
2.4
1.8
1.2
0.6
0
0
25
5
Tj-Junction Temperature


Drain Current @ Tj
Drain Current(A)
12
10
8.0
6.0
4.0
2.0
0
0
25
5
Tj-Junction Temperature


Thermal Transient Impedance
Normalized Transient
Thermal Resistance
10
1
0.1
0.01
0.001
0.0001
0.001
0.01
0.1
1
10
100
1000
In Descending order
D=0.5, 0.3, 0.1,0.05,0.02,0.01
Single Pulse

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